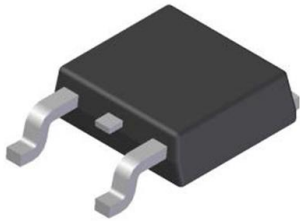


# DMT6009LK3-13 Datasheet

[www.digi-electronics.com](http://www.digi-electronics.com)



<https://www.DiGi-Electronics.com>

|                              |  |
|------------------------------|--|
| DiGi Electronics Part Number | DMT6009LK3-13-DG   |
| Manufacturer                 | <a href="#">Diodes Incorporated</a>                                  |
| Manufacturer Product Number  | DMT6009LK3-13  |
| Description                  | MOSFET N-CH 60V 13.3A/57A TO252                                      |
| Detailed Description         | N-Channel 60 V 13.3A (Ta), 57A (Tc) 2.6W (Ta) Surface Mount TO-252-3 |



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

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## Purchase and inquiry

Manufacturer Product Number:

DMT6009LK3-13

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

60 V

Drive Voltage (Max Rds On, Min Rds On):

4.5V, 10V

Vgs(th) (Max) @ Id:

2V @ 250 $\mu$ A

Vgs (Max):

$\pm$ 16V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

TO-252-3

Base Product Number:

DMT6009

Manufacturer:

Diodes Incorporated

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

13.3A (Ta), 57A (Tc)

Rds On (Max) @ Id, Vgs:

10mOhm @ 13.5A, 10V

Gate Charge (Qg) (Max) @ Vgs:

33.5 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

1925 pF @ 30 V

Power Dissipation (Max):

2.6W (Ta)

Mounting Type:

Surface Mount

Package / Case:

TO-252-3, DPAK (2 Leads + Tab), SC-63

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



DMT6009LK3

60V N-CHANNEL ENHANCEMENT MODE MOSFET

## Product Summary

| $BV_{DSS}$ | $R_{DS(ON)}$ Max                 | $I_D$ Max<br>$T_C = +25^\circ C$ |
|------------|----------------------------------|----------------------------------|
| 60V        | 10m $\Omega$ @ $V_{GS} = 10V$    | 57A                              |
|            | 12.8m $\Omega$ @ $V_{GS} = 4.5V$ | 51A                              |

## Features

- Low  $R_{DS(ON)}$  – Ensures On State Losses Are Minimized
- Excellent  $Q_{gd} \times R_{DS(ON)}$  Product (FOM)
- Advanced Technology for DC/DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high- efficiency power management applications.

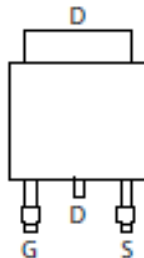
- Power Management Functions
- DC-DC Converters
- Backlighting

## Mechanical Data

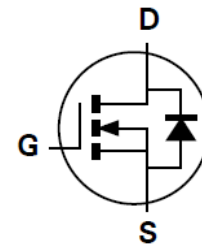
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208  $\text{e3}$
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top View



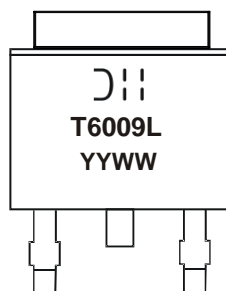
Equivalent Circuit

## Ordering Information (Note 4)

| Part Number   | Case  | Packaging         |
|---------------|-------|-------------------|
| DMT6009LK3-13 | TO252 | 2,500/Tape & Reel |

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



$\text{D}$  = Manufacturer's Marking  
 T6009L = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 15 = 2015)  
 WW = Week Code (01 to 53)



DMT6009LK3

### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic  | Symbol           | Value                  | Unit |
|---|------------------|------------------------|------|
| Drain-Source Voltage                                    | V <sub>DSS</sub> | 60                     | V    |
| Gate-Source Voltage                                     | V <sub>GSS</sub> | ±16                    | V    |
| Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V | I <sub>D</sub>   | T <sub>A</sub> = +25°C | 13.3 |
|   |                  | T <sub>A</sub> = +70°C | 10.6 |
| Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V | I <sub>D</sub>   | T <sub>C</sub> = +25°C | 57   |
|   |                  | T <sub>C</sub> = +70°C | 46   |
| Maximum Continuous Body Diode Forward Current (Note 6)  | I <sub>S</sub>   | 80                     | A    |
| Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)      | I <sub>DM</sub>  | 90                     | A    |
| Avalanche Current, L=0.1mH                              | I <sub>AS</sub>  | 20.3                   | A    |
| Avalanche Energy, L=0.1mH                               | E <sub>AS</sub>  | 20.6                   | mJ   |

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                   | Symbol                            | Value       | Unit |
|--|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5)                 | P <sub>D</sub>                    | 2.6         | W    |
| Thermal Resistance, Junction to Ambient (Note 5) | R <sub>θJA</sub>                  | 47          | °C/W |
| Total Power Dissipation (Note 6)                 | P <sub>D</sub>                    | 50          | W    |
| Thermal Resistance, Junction to Case (Note 6)    | R <sub>θJC</sub>                  | 2.5         | °C/W |
| Operating and Storage Temperature Range          | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                             | Symbol              | Min | Typ   | Max  | Unit | Test Condition   |
|--|---------------------|-----|-------|------|------|--|
| <b>OFF CHARACTERISTICS (Note 7)</b>        |                     |     |       |      |      |  |
| Drain-Source Breakdown Voltage             | BV <sub>DSS</sub>   | 60  | -     | -    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA   |
| Zero Gate Voltage Drain Current            | I <sub>DSS</sub>    | -   | -     | 1    | μA   | V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V  |
| Gate-Source Leakage                        | I <sub>GSS</sub>    | -   | -     | ±100 | nA   | V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0V   |
| <b>ON CHARACTERISTICS (Note 7)</b>         |                     |     |       |      |      |  |
| Gate Threshold Voltage                     | V <sub>GS(TH)</sub> | 0.7 | 1.4   | 2    | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA                                   |
| Static Drain-Source On-Resistance          | R <sub>DS(ON)</sub> | -   | 8.3   | 10   | mΩ   | V <sub>GS</sub> = 10V, I <sub>D</sub> = 13.5A  |
|  |                     | -   | 9.6   | 12.8 | mΩ   | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 11.5A   |
| Diode Forward Voltage                      | V <sub>SD</sub>     | -   | 0.9   | 1.2  | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A   |
| <b>DYNAMIC CHARACTERISTICS (Note 8)</b>    |                     |     |       |      |      |  |
| Input Capacitance                          | C <sub>iss</sub>    | -   | 1,925 | -    | pF   | V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V,<br>f = 1MHz                                     |
| Output Capacitance                         | C <sub>oss</sub>    | -   | 438   | -    |      |  |
| Reverse Transfer Capacitance               | C <sub>rss</sub>    | -   | 41    | -    |      |  |
| Gate Resistance                            | R <sub>g</sub>      | -   | 1.7   | -    | Ω    | V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz   |
| Total Gate Charge (V <sub>GS</sub> = 4.5V) | Q <sub>g</sub>      | -   | 15.6  | -    | nC   | V <sub>DS</sub> = 30V, I <sub>D</sub> = 13.5A  |
| Total Gate Charge (V <sub>GS</sub> = 10V)  | Q <sub>g</sub>      | -   | 33.5  | -    |      |  |
| Gate-Source Charge                         | Q <sub>gs</sub>     | -   | 4.7   | -    |      |  |
| Gate-Drain Charge                          | Q <sub>gd</sub>     | -   | 5.3   | -    |      |  |
| Turn-On Delay Time                         | t <sub>D(ON)</sub>  | -   | 4.5   | -    | ns   | V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V,<br>R <sub>G</sub> = 6Ω, I <sub>D</sub> = 13.5A |
| Turn-On Rise Time                          | t <sub>R</sub>      | -   | 8.6   | -    |      |  |
| Turn-Off Delay Time                        | t <sub>D(OFF)</sub> | -   | 35.9  | -    |      |  |
| Turn-Off Fall Time                         | t <sub>F</sub>      | -   | 15.7  | -    |      |  |
| Body Diode Reverse Recovery Time           | t <sub>RR</sub>     | -   | 18.2  | -    | ns   | I <sub>F</sub> = 13.5A, di/dt = 400A/μs  |
| Body Diode Reverse Recovery Charge         | Q <sub>RR</sub>     | -   | 33.1  | -    | nC   |  |

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
  - Device mounted on infinite heat sink and measured by thermal couple attached on bottom heat sink of package.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.



**DMT6009LK3**

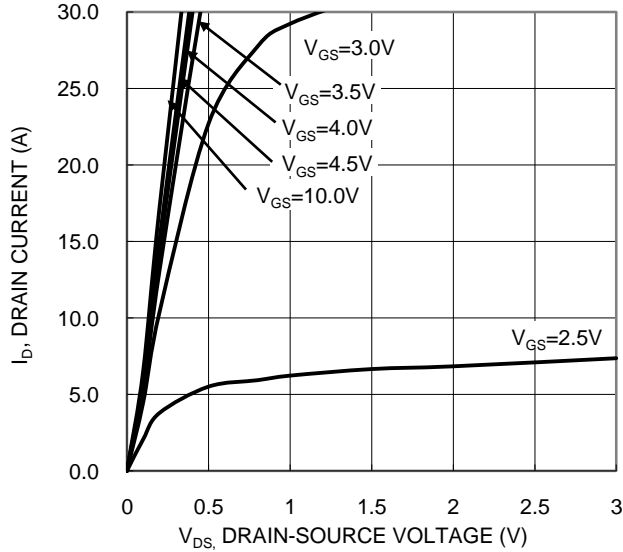


Figure 1. Typical Output Characteristic

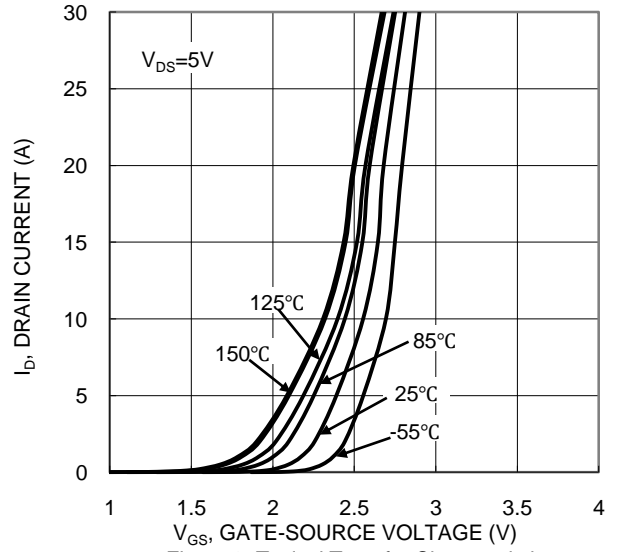


Figure 2. Typical Transfer Characteristic

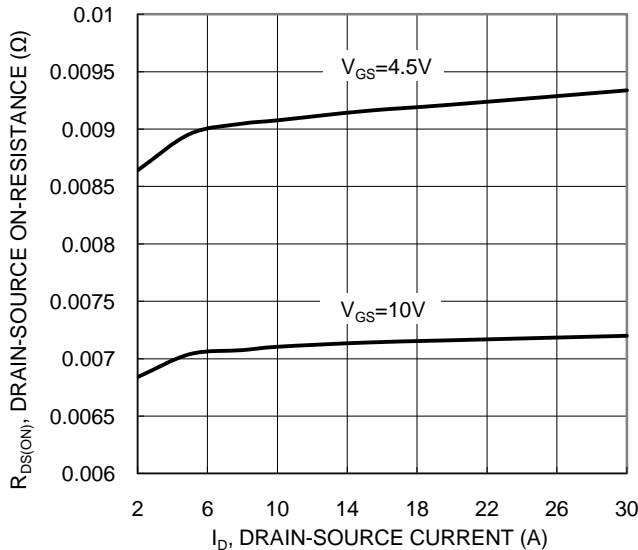


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

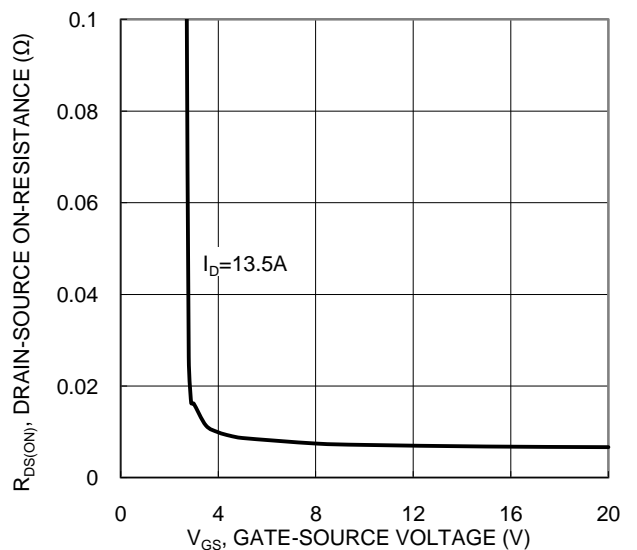


Figure 4. Typical Transfer Characteristic

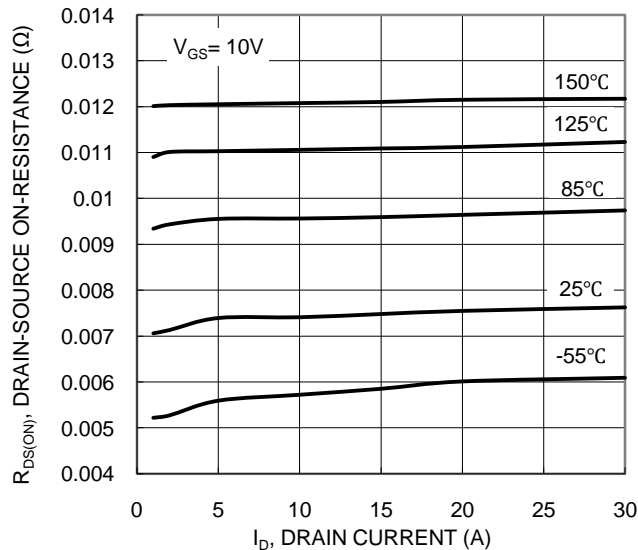


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

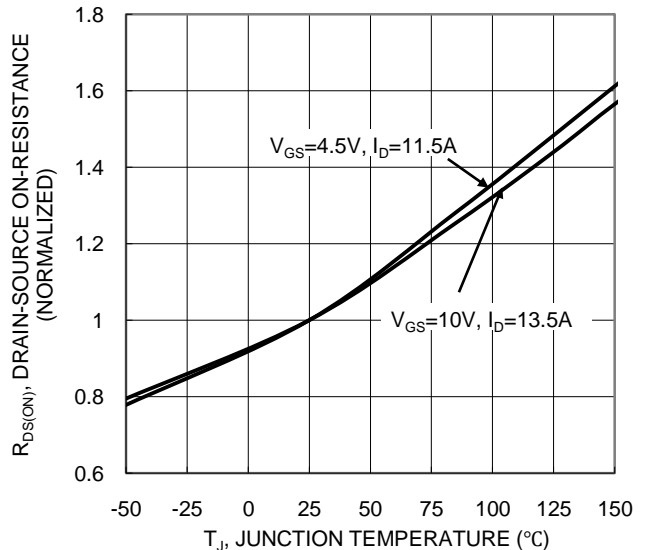


Figure 6. On-Resistance Variation with Junction Temperature



**DMT6009LK3**

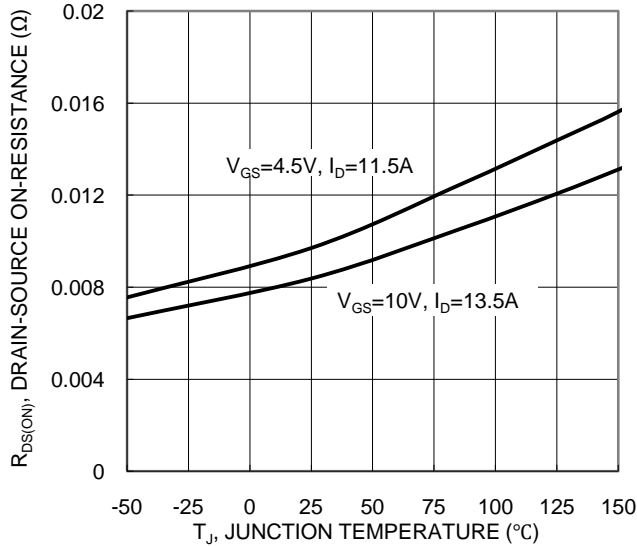


Figure 7. On-Resistance Variation with Junction Temperature

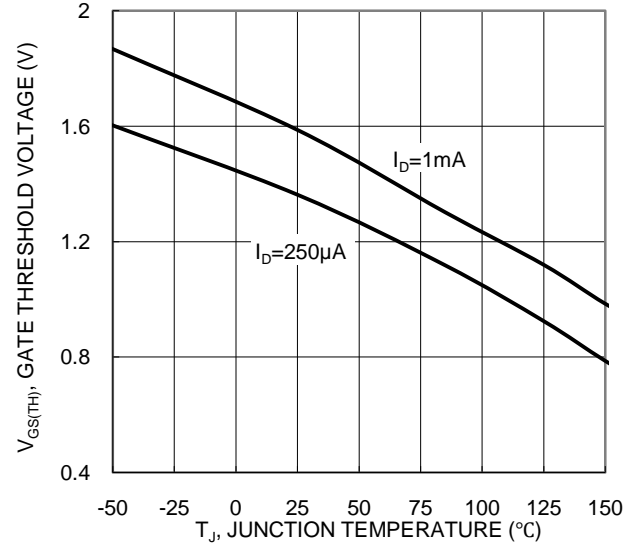


Figure 8. Gate Threshold Variation vs. Junction Temperature

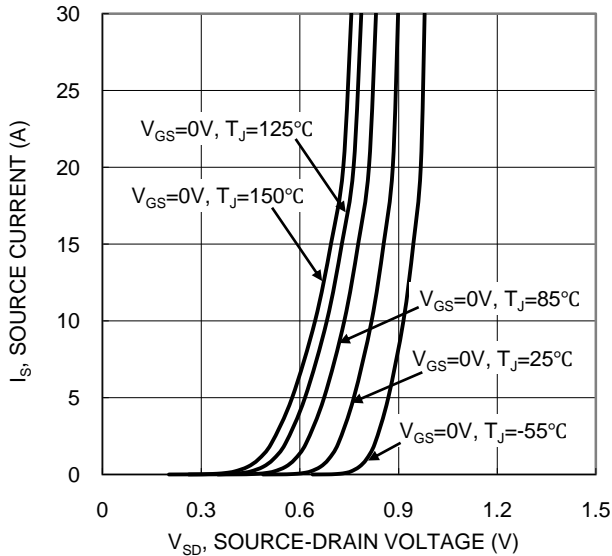


Figure 9. Diode Forward Voltage vs. Current

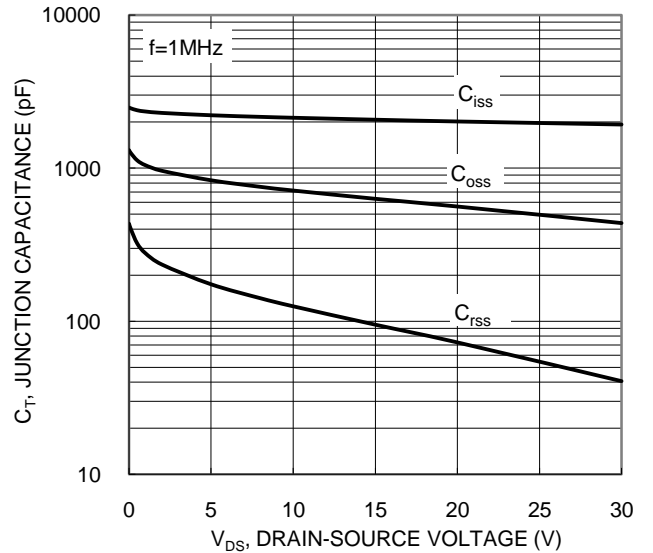


Figure 10. Typical Junction Capacitance

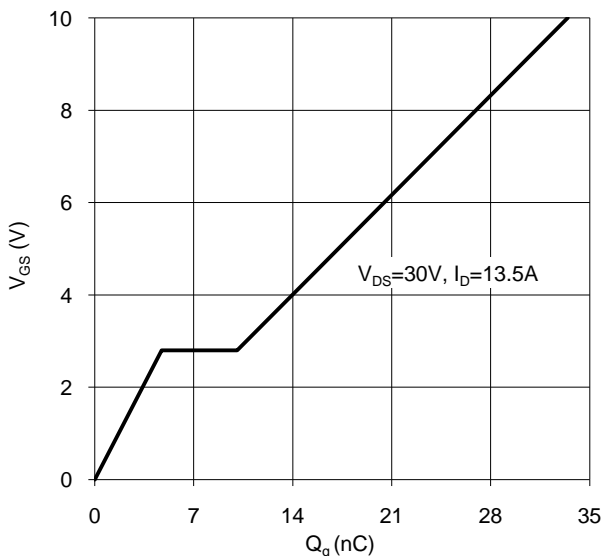


Figure 11. Gate Charge

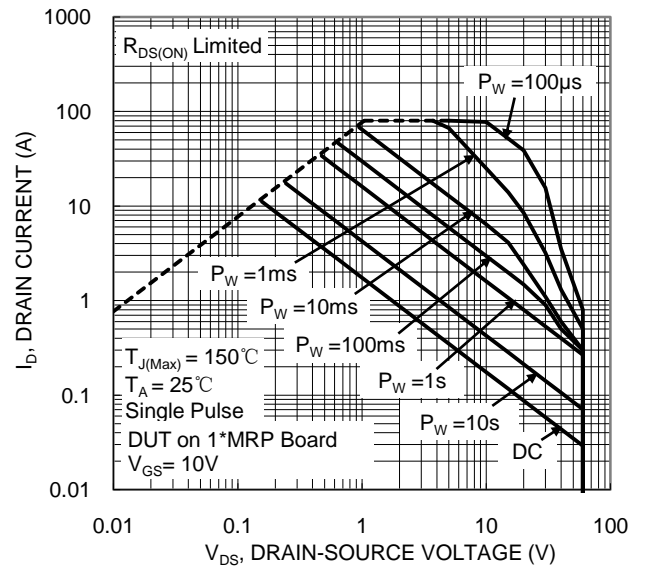


Figure 12. SOA, Safe Operation Area



**DMT6009LK3**

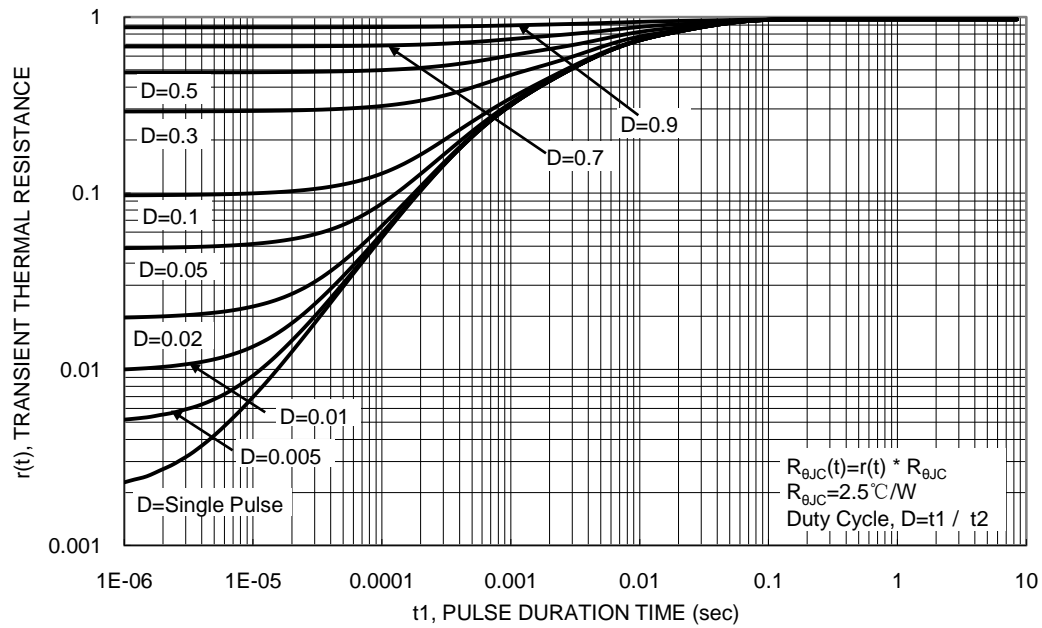
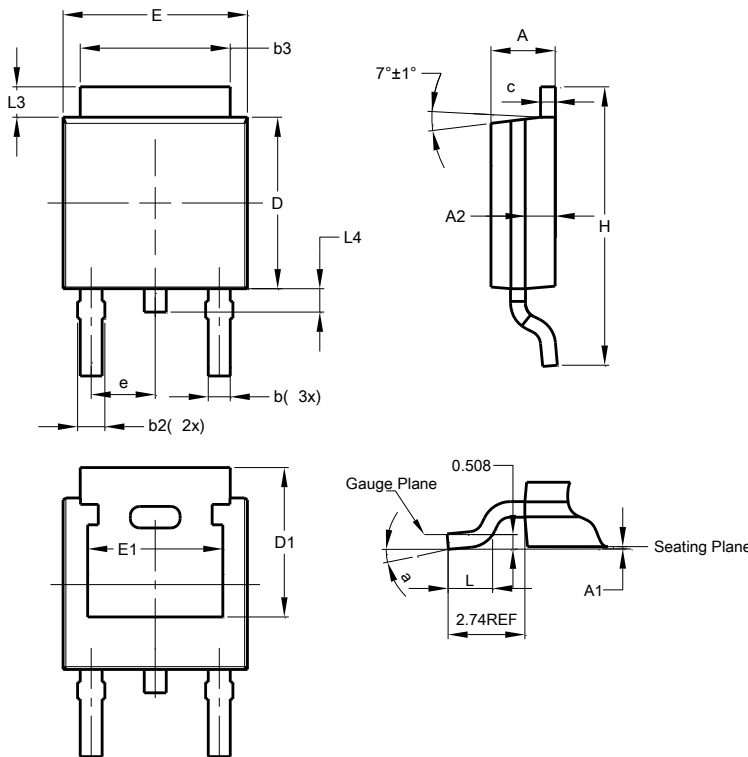


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

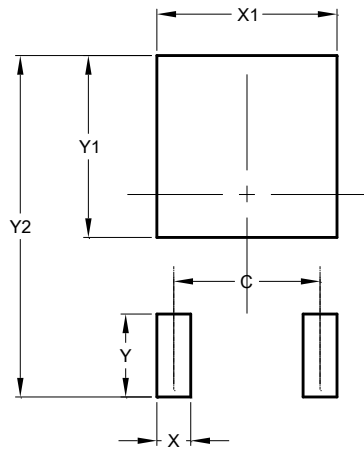
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



| TO252 (DPAK)                |      |       |       |
|-----------------------------|------|-------|-------|
| Dim                         | Min  | Max   | Typ   |
| A                           | 2.19 | 2.39  | 2.29  |
| A1                          | 0.00 | 0.13  | 0.08  |
| A2                          | 0.97 | 1.17  | 1.07  |
| b                           | 0.64 | 0.88  | 0.783 |
| b2                          | 0.76 | 1.14  | 0.95  |
| b3                          | 5.21 | 5.46  | 5.33  |
| c                           | 0.45 | 0.58  | 0.531 |
| D                           | 6.00 | 6.20  | 6.10  |
| D1                          | 5.21 | -     | -     |
| e                           | -    | -     | 2.286 |
| E                           | 6.45 | 6.70  | 6.58  |
| E1                          | 4.32 | -     | -     |
| H                           | 9.40 | 10.41 | 9.91  |
| L                           | 1.40 | 1.78  | 1.59  |
| L3                          | 0.88 | 1.27  | 1.08  |
| L4                          | 0.64 | 1.02  | 0.83  |
| a                           | 0°   | 10°   | -     |
| <b>All Dimensions in mm</b> |      |       |       |

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 4.572         |
| X          | 1.060         |
| X1         | 5.632         |
| Y          | 2.600         |
| Y1         | 5.700         |
| Y2         | 10.700        |

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